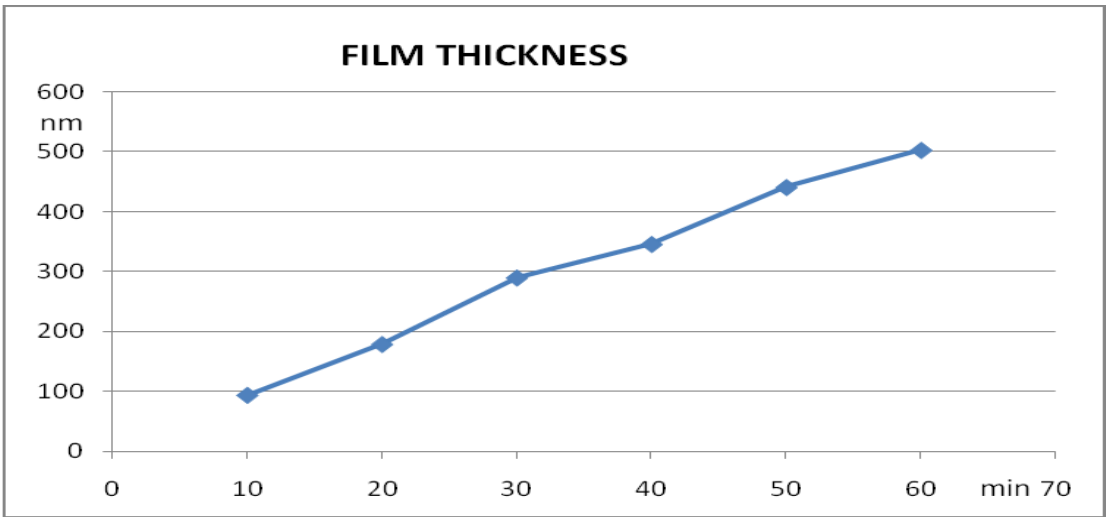
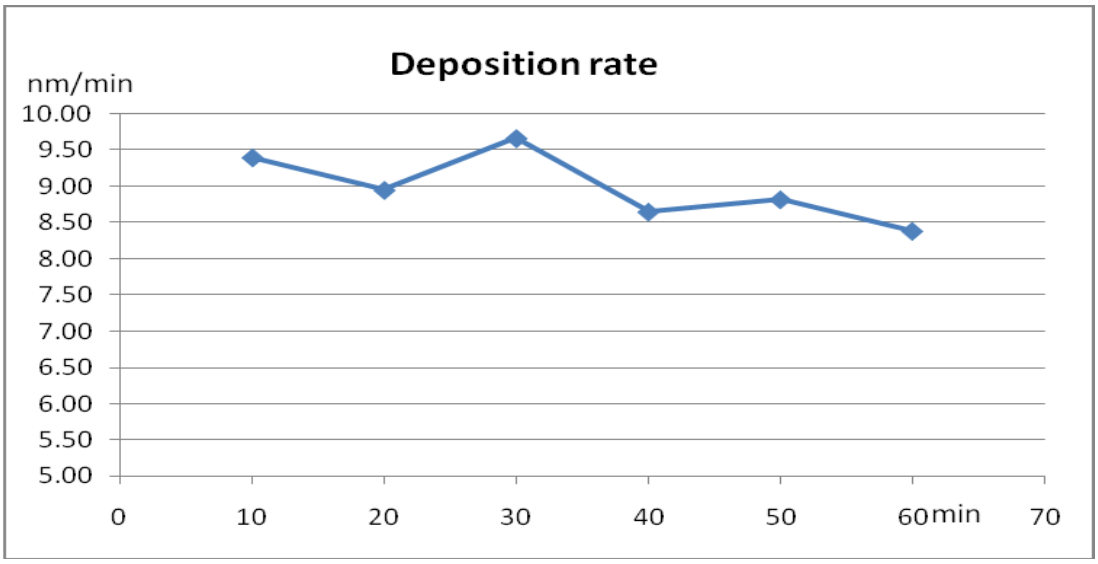
LPCVD	Tube 4	**Material**	Low Temperature Oxide	
Comments:	Film Uniformity Variance < 2% at centre and very high at the edges across 4” wafer			
Gases	**Flow Rate**	**Time(minutes)**	**Film Thickness(nm)**	**Deposition rate (nm/min)**
Temperature	450 C	10	94	9.40
Comments:		20	179	8.95
		30	290	9.67
		40	346	8.65
		50	441	8.82
		60	503	8.38





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